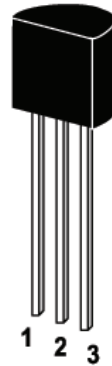


**PNP Silicon Epitaxial Planar Transistor**  
for amplifier applications

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector

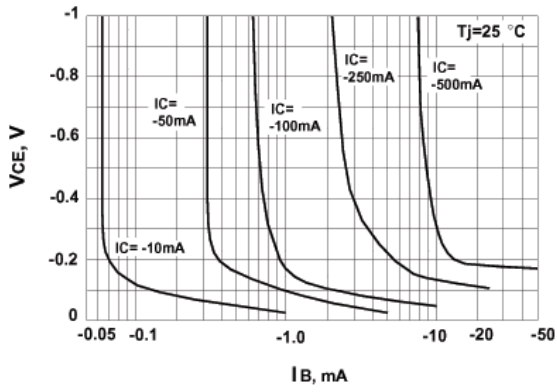
TO-92 Plastic Package  
Weight approx. 0.19g

**Absolute Maximum Ratings\* (T<sub>a</sub> = 25 °C)**

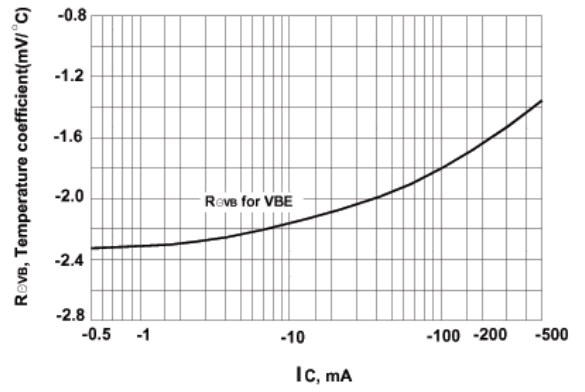
	Symbol	Value	Unit
Collector Base Voltage	-V <sub>CBO</sub>	80	V
Collector Emitter Voltage	-V <sub>CEO</sub>	80	V
Emitter Base Voltage	-V <sub>EBO</sub>	4.0	V
Collector Current	-I <sub>C</sub>	500	mA
Total Device Dissipation at T <sub>a</sub> =25°C Derate above 25°C	P <sub>tot</sub>	625 5	mW mW/°C
Total Device Dissipation at T <sub>c</sub> =25°C Derate above 25°C	P <sub>tot</sub>	1.5 12	W mW/°C
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	83.3	°C/W
Thermal Resistance, Junction to Ambient(Note1)	R <sub>θJA</sub>	200	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>S</sub>	-55 to +150	°C

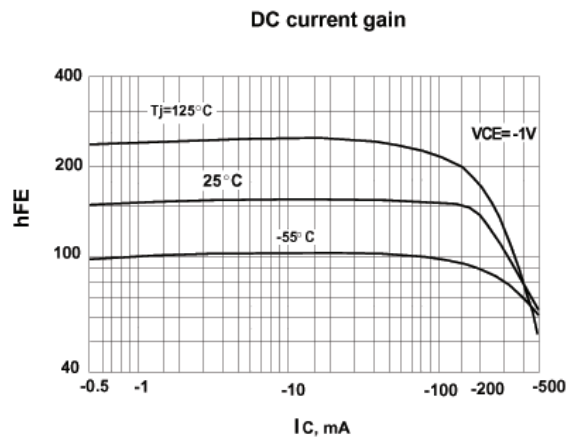
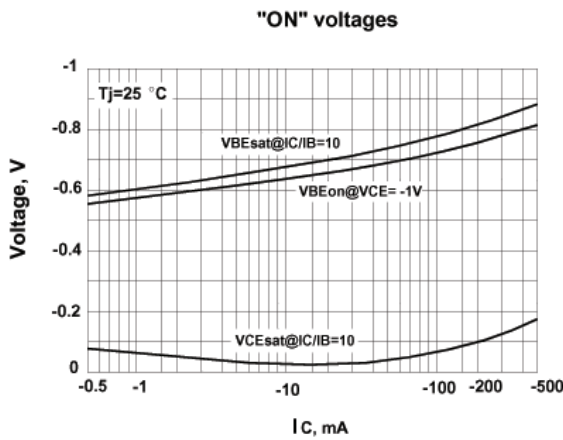
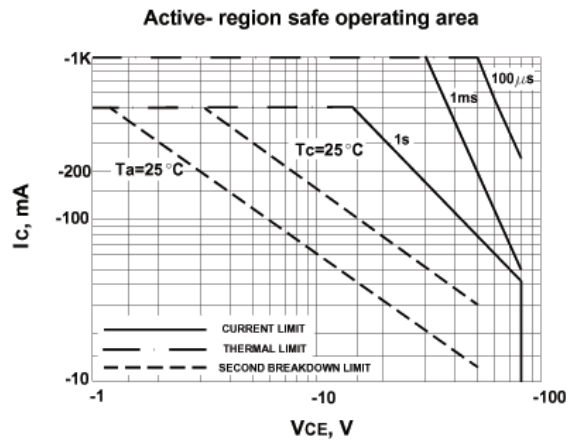
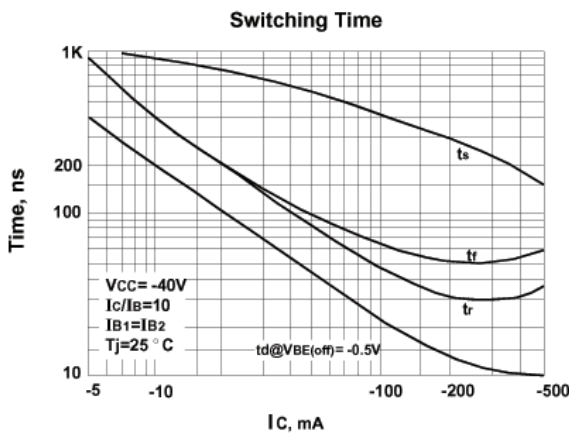
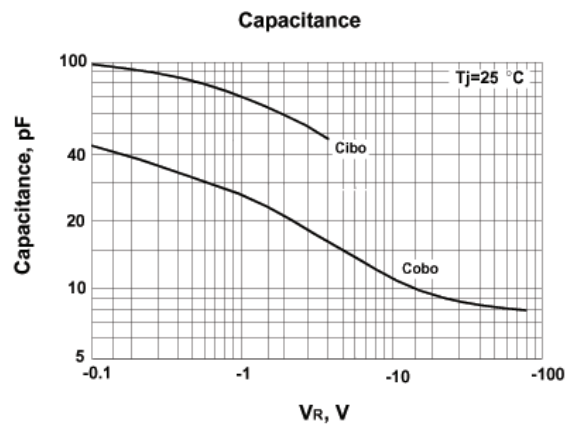
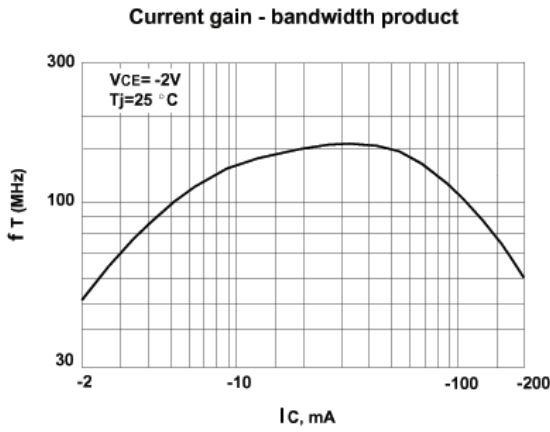
1.R<sub>θJA</sub> is measured with the device soldered into a typical printed circuit board.

Collector saturation region



Base emitter temperature coefficient





**Characteristics at  $T_{amb}=25\text{ }^{\circ}\text{C}$** 

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-I_C=10\text{mA}$ , $-V_{CE}=1\text{V}$	$h_{FE}$	100	-	-	-
at $-I_C=100\text{mA}$ , $-V_{CE}=1\text{V}$	$h_{FE}$	100	-	-	-
Collector Cutoff Current					
at $-V_{CB}=80\text{V}$	$-I_{CBO}$	-	-	0.1	$\mu\text{A}$
Collector Cutoff Current					
at $-V_{CE}=60\text{V}$	$-I_{CES}$	-	-	0.1	$\mu\text{A}$
Collector Emitter Breakdown Voltage <sup>1)</sup>					
at $-I_C=1\text{mA}$	$-V_{(BR)CEO}$	80	-	-	V
Emitter Base Breakdown Voltage					
at $-I_E=100\mu\text{A}$	$-V_{(BR)EBO}$	4	-	-	V
Collector Saturation Voltage					
at $-I_C=100\text{mA}$ , $-I_B=10\text{mA}$	$-V_{CE(sat)}$	-	-	0.25	V
Base On Voltage					
at $-I_C=100\text{mA}$ , $-V_{CE}=1\text{V}$	$-V_{BE(on)}$	-	-	1.2	V
Current Gain – Bandwidth Product <sup>2)</sup>					
at $-I_C=100\text{mA}$ , $-V_{CE}=1\text{V}$ , $f=100\text{MHz}$	$f_T$	50	-	-	MHz

1) Pulse test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

2)  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.

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